

Thyristor \ Diode Module

$$V_{RRM} = 2 \times 1800 \text{ V}$$

$$I_{TAV} = 260 \text{ A}$$

$$V_T = 1.06 \text{ V}$$

Phase leg

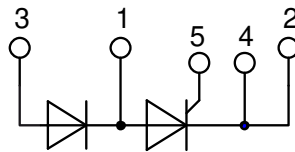
Part number

MCMA260PD1800YB



Backside: isolated

 E72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al₂O₃-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: Y4

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Disclaimer Notice

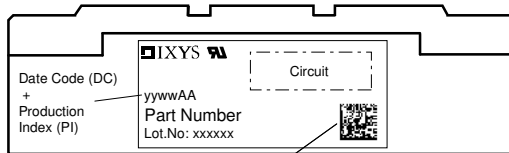
Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.



Rectifier			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1900	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1800	V
I_{RD}	reverse current, drain current	$V_{R/D} = 1800 V$	$T_{VJ} = 25^{\circ}C$		300	μA
		$V_{R/D} = 1800 V$	$T_{VJ} = 140^{\circ}C$		20	mA
V_T	forward voltage drop	$I_T = 200 A$	$T_{VJ} = 25^{\circ}C$		1.12	V
		$I_T = 400 A$			1.33	V
		$I_T = 200 A$	$T_{VJ} = 125^{\circ}C$		1.06	V
		$I_T = 400 A$			1.31	V
I_{TAV}	average forward current	$T_C = 85^{\circ}C$	$T_{VJ} = 140^{\circ}C$		260	A
$I_{T(RMS)}$	RMS forward current	180° sine			408	A
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 140^{\circ}C$		0.81	V
r_T	slope resistance				1.23	m Ω
R_{thJC}	thermal resistance junction to case				0.13	K/W
R_{thCH}	thermal resistance case to heatsink			0.07		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		880	W
I_{TSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		8.30	kA
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		8.97	kA
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 140^{\circ}C$		7.06	kA
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		7.62	kA
I^2t	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		344.5	kA ² s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		334.3	kA ² s
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 140^{\circ}C$		248.9	kA ² s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		241.6	kA ² s
C_J	junction capacitance	$V_R = 400 V \quad f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		366	pF
P_{GM}	max. gate power dissipation	$t_p = 30 \mu s$	$T_C = 140^{\circ}C$		120	W
		$t_p = 500 \mu s$			60	W
P_{GAV}	average gate power dissipation				20	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 140^{\circ}C; f = 50 \text{ Hz}$	repetitive, $I_T = 780 A$		100	A/ μs
		$t_p = 200 \mu s; di_G/dt = 0.5 A/\mu s;$	non-repet., $I_T = 260 A$		500	A/ μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^{\circ}C$		1000	V/ μs
		$R_{GK} = \infty; \text{method 1 (linear voltage rise)}$				
V_{GT}	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		2	V
			$T_{VJ} = -40^{\circ}C$		3	V
I_{GT}	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		150	mA
			$T_{VJ} = -40^{\circ}C$		220	mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^{\circ}C$		0.25	V
I_{GD}	gate non-trigger current				10	mA
I_L	latching current	$t_p = 30 \mu s$	$T_{VJ} = 25^{\circ}C$		200	mA
		$I_G = 0.5 A; di_G/dt = 0.5 A/\mu s$				
I_H	holding current	$V_D = 6 V \quad R_{GK} = \infty$	$T_{VJ} = 25^{\circ}C$		150	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}C$		2	μs
		$I_G = 0.5 A; di_G/dt = 0.5 A/\mu s$				
t_q	turn-off time	$V_R = 100 V; I_T = 260 A; V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125^{\circ}C$		200	μs
		$di/dt = 10 A/\mu s \quad dv/dt = 50 V/\mu s \quad t_p = 200 \mu s$				



Package Y4				Ratings		
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			300	A
T_{VJ}	virtual junction temperature		-40		140	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		125	°C
Weight					150	g
M_D	mounting torque		2.25		2.75	Nm
M_T	terminal torque		4.5		5.5	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	14.0	10.0		mm
$d_{Spb/Apb}$		terminal to backside	16.0	16.0		mm
V_{ISOL}	isolation voltage	t = 1 second	4800			V
		t = 1 minute	4000			V



Data Matrix: part no. (1-19), DC + PI (20-25), lot.no.# (26-31), blank (32), serial no.# (33-36)

Part description

- M = Module
- C = Thyristor (SCR)
- M = Thyristor
- A = (up to 1800V)
- 260 = Current Rating [A]
- PD = Phase leg
- 1800 = Reverse Voltage [V]
- YB = Y4-M6

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCMA260PD1800YB	MCMA260PD1800YB	Box	6	515579

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 140\text{ °C}$



Thyristor

$V_{0\ max}$	threshold voltage	0.81	V
$R_{0\ max}$	slope resistance *	0.59	mΩ



Outlines Y4



Dim.	MIN [mm]	MAX [mm]	MIN [inch]	MAX [inch]
a	30.0	30.6	1.181	1.205
b	typ. 0.25		typ. 0.010	
c	64.0	65.0	2.520	2.559
d	6.5	7.0	0.256	0.275
e	4.9	5.1	0.193	0.201
f	28.6	29.2	1.126	1.150
g	7.3	7.7	0.287	0.303
h	93.5	94.5	3.681	3.720
i	79.5	80.5	3.130	3.169
j	4.8	5.2	0.189	0.205
k	33.4	34.0	1.315	1.339
l	16.7	17.3	0.657	0.681
m	22.7	23.3	0.894	0.917
n	22.7	23.3	0.894	0.917
o	14.0	15.0	0.551	0.591
p	typ. 10.5		typ. 0.413	
r	1.8	2.4	0.071	0.041

Optional accessories for modules
Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red
Type ZY 180L (L = Left for pin pair 4/5) UL 758, style 3751



Thyristor

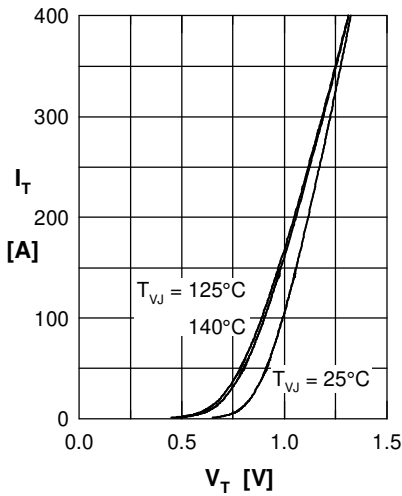


Fig. 1 Forward current vs. voltage drop per thyristor

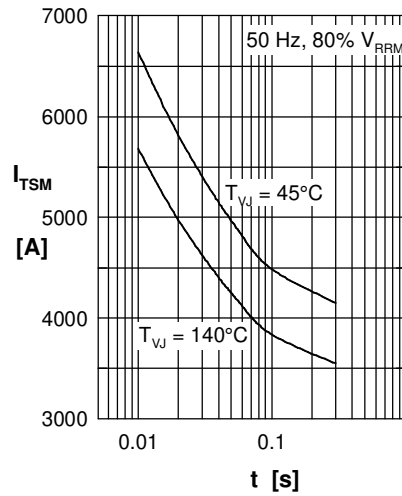


Fig. 2 Surge overload current vs. time per thyristor

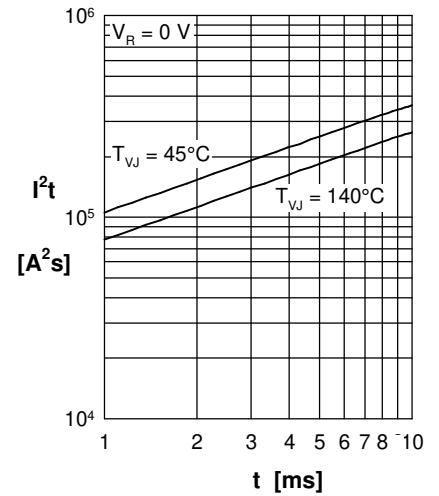


Fig. 3 I^2t vs. time per thyristor

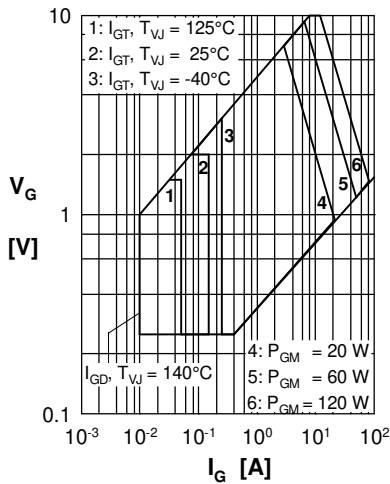


Fig. 4 Gate voltage & gate current

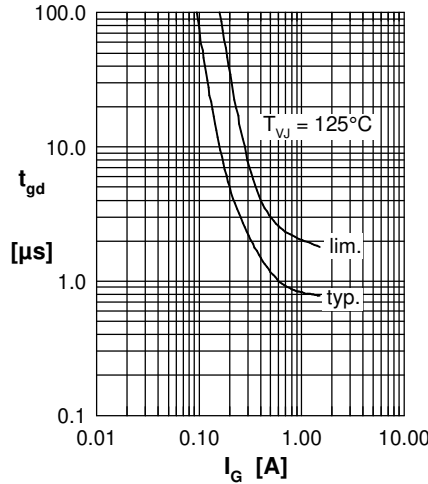


Fig. 5 Gate controlled delay time t_{gd}

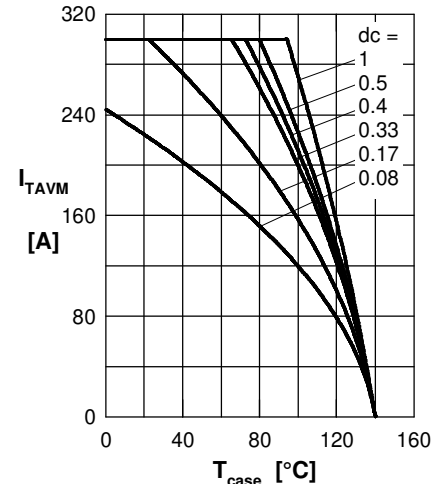


Fig. 6 Max. forward current vs. case temperature per thyristor.

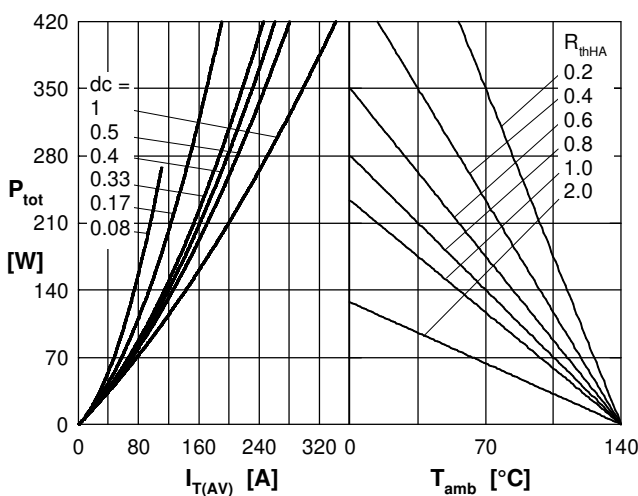


Fig. 7 Power dissipation vs. forward current and ambient temperature per thyristor

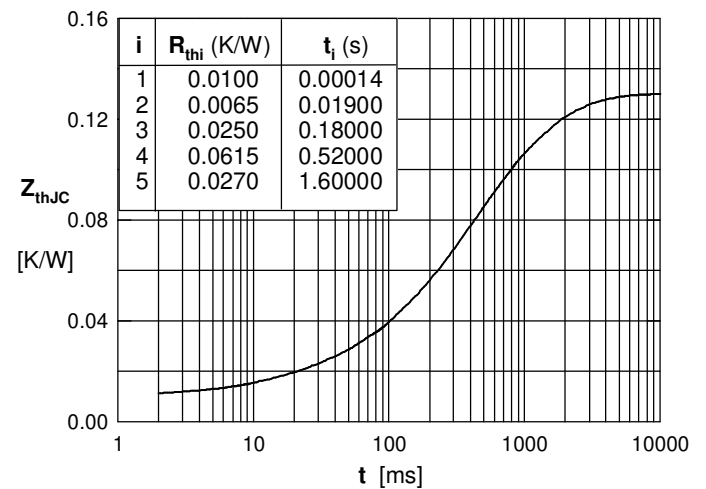


Fig. 8 Transient thermal impedance junction to case vs. time per thyristor